

Stabilized etching solutions for Cu and Cu/Ni layers

Abstract

- 5 The present invention relates to new storage-stable solutions which can be used in semiconductor technology to effect specific etching of copper metallization layers and also Cu/Ni layers. With the new etch solutions it is possible to carry out etching and patterning of all-copper metallizations, layers of copper/nickel alloys, and also successive copper and nickel layers.